

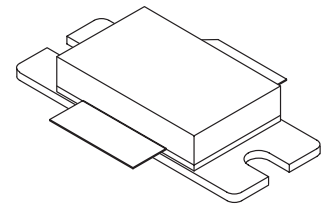
The RF MOSFET Line
RF Power Field Effect Transistors
N-Channel Enhancement-Mode Lateral MOSFETs

Designed for Class AB PCN and PCS base station applications with frequencies from 1.9 to 2.0 GHz. Suitable for CDMA, TDMA, GSM, and multicarrier amplifier applications.

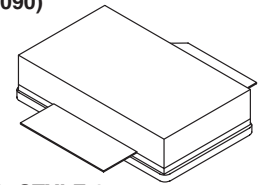
- Typical CDMA Performance: 1990 MHz, 26 Volts
IS-97 CDMA Pilot, Sync, Paging, Traffic Codes 8 Through 13
Output Power — 9 Watts
Power Gain — 10 dB
Adjacent Channel Power —
885 kHz: -47 dBc @ 30 kHz BW
1.25 MHz: -55 dBc @ 12.5 kHz BW
2.25 MHz: -55 dBc @ 1 MHz BW
- Internally Matched, Controlled Q, for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 1.93 GHz, 90 Watts (CW) Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Available in Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF19090
MRF19090S
MRF19090SR3

1990 MHz, 90 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465B-03, STYLE 1
(NI-880)
(MRF19090)



CASE 465C-02, STYLE 1
(NI-880S)
(MRF19090S)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	65	Vdc
Gate-Source Voltage	V_{GS}	+15, -0.5	Vdc
Total Device Dissipation @ $T_C > = 25^\circ\text{C}$ Derate above 25°C	P_D	270 1.54	Watts W/°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Operating Junction Temperature	T_J	200	°C

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)

THERMAL CHARACTERISTICS

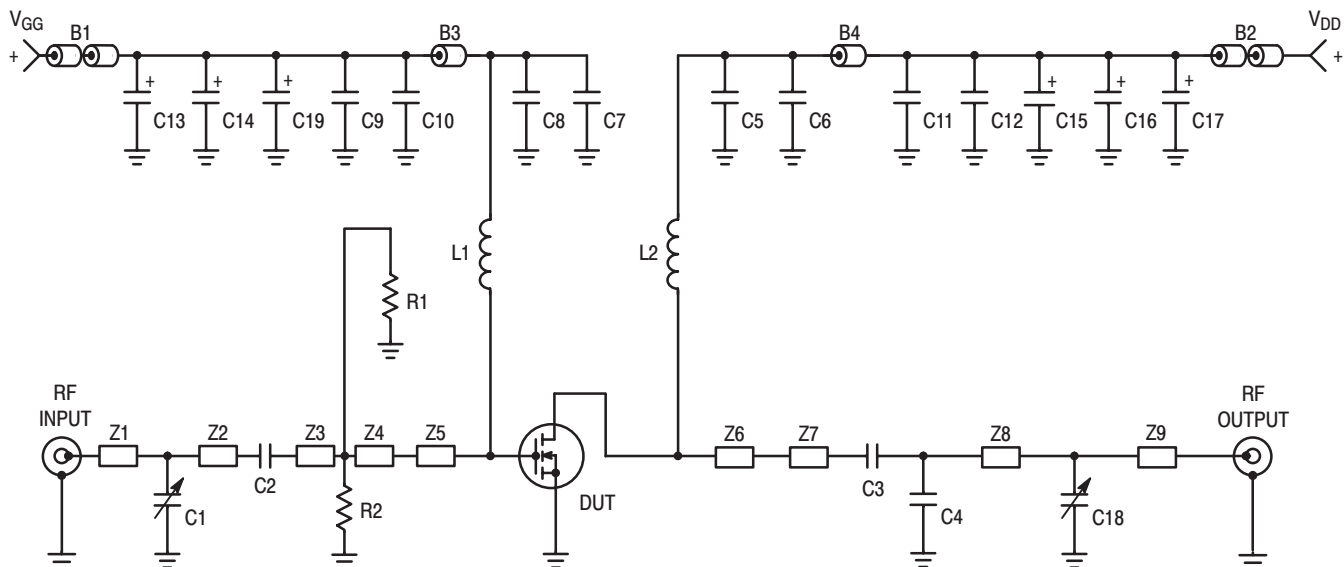
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.65	°C/W

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 100\ \mu\text{A}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μA dc
Gate–Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μA dc
ON CHARACTERISTICS					
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 3\text{ A}$ dc)	g_{fs}	—	7.2	—	S
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\ \mu\text{A}$ dc)	$V_{GS(th)}$	2.0	—	4.0	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 750\text{ mA}$ dc)	$V_{GS(Q)}$	2.5	3.8	4.5	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1\text{ A}$ dc)	$V_{DS(on)}$	—	0.10	—	Vdc
DYNAMIC CHARACTERISTICS					
Reverse Transfer Capacitance (1) ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	—	4.2	—	pF
FUNCTIONAL TESTS (In Motorola Test Fixture)					
Two–Tone Common–Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 750\text{ mA}$, $f = 1930\text{ MHz}$ and 1990 MHz , Tone Spacing = 100 kHz)	G_{ps}	10	11.5	—	dB
Two–Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 750\text{ mA}$, $f = 1930\text{ MHz}$ and 1990 MHz , Tone Spacing = 100 kHz)	η	33	35	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 750\text{ mA}$, $f = 1930\text{ MHz}$ and 1990 MHz , Tone Spacing = 100 kHz)	IMD	—	–30	–28	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 750\text{ mA}$, $f = 1930\text{ MHz}$ and 1990 MHz , Tone Spacing = 100 kHz)	IRL	—	–12	—	dB
P_{out} , 1 dB Compression Point ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W CW}$, $f = 1990\text{ MHz}$)	P1dB	—	90	—	W
Output Mismatch Stress ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W CW}$, $I_{DQ} = 750\text{ mA}$, $f = 1930\text{ MHz}$, VSWR = 10:1, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power Before and After Test			

(1) Part is internally matched both on input and output.



B1, B2	2 Ferrite Beads, Round, Ferroxcube #56-590-65-3B	L1, L2	8 Turns, #26 AWG, 0.085" OD, 0.330" Long, Copper Wire
B3, B34	Ferrite Beads, Surface Mount, Ferroxcube	R1, R2	270 Ω , 1/4 W Chip Resistors, Garrett Instruments #RM73B2B271JT
C1, C18	0.4 - 2.5 pF Variable Capacitors, Johanson Gigatrim #27285	Z1	ZO = 50 Ohms
C2, C5, C8	10 pF Chip Capacitors, B Case, ATC #100B100CCA500X	Z2	ZO = 50 Ohms, Lambda = 0.123
C3	12 pF Chip Capacitor, B Case, ATC #100B120CCA500X	Z3	ZO = 15.24 Ohms, Lambda = 0.0762
C4	0.3 pF Chip Capacitor, B Case, ATC #100B0R3CCA500X	Z4	ZO = 10.11 Ohms, Lambda = 0.0392
C6, C7	120 pF Chip Capacitors, B Case, ATC #100B12R1CCA500X	Z5	ZO = 6.34 Ohms, Lambda = 0.0711
C9, C12	0.1 μ F Chip Capacitors, Kemet #CDR33BX104AKWS	Z6	ZO = 5.02 Ohms, Lambda = 0.0476
C10, C11	1000 pF Chip Capacitors, B Case, ATC #100B102JCA50X	Z7	ZO = 5.54 Ohms, Lambda = 0.0972
C13, C17	22 μ F, 35 V Tantalum Chip Capacitors, Kemet #T491X226K035AS4394	Z8	ZO = 50.0 Ohms, Lambda = 0.194
C14, C16	10 μ F, 35 V Tantalum Chip Capacitors, Kemet #T495X106K035AS4394	Z9	ZO = 50.0 Ohms
C15, C19	1 μ F, 35 V Tantalum Chip Capacitors, Kemet #T495X105K035AS4394	Raw PCB Material	0.030" Glass Teflon [®] , $\epsilon_r = 2.55$, 2 oz Copper, 3" x 5" Dimensions

Figure 1. MRF19090 Test Circuit Schematic

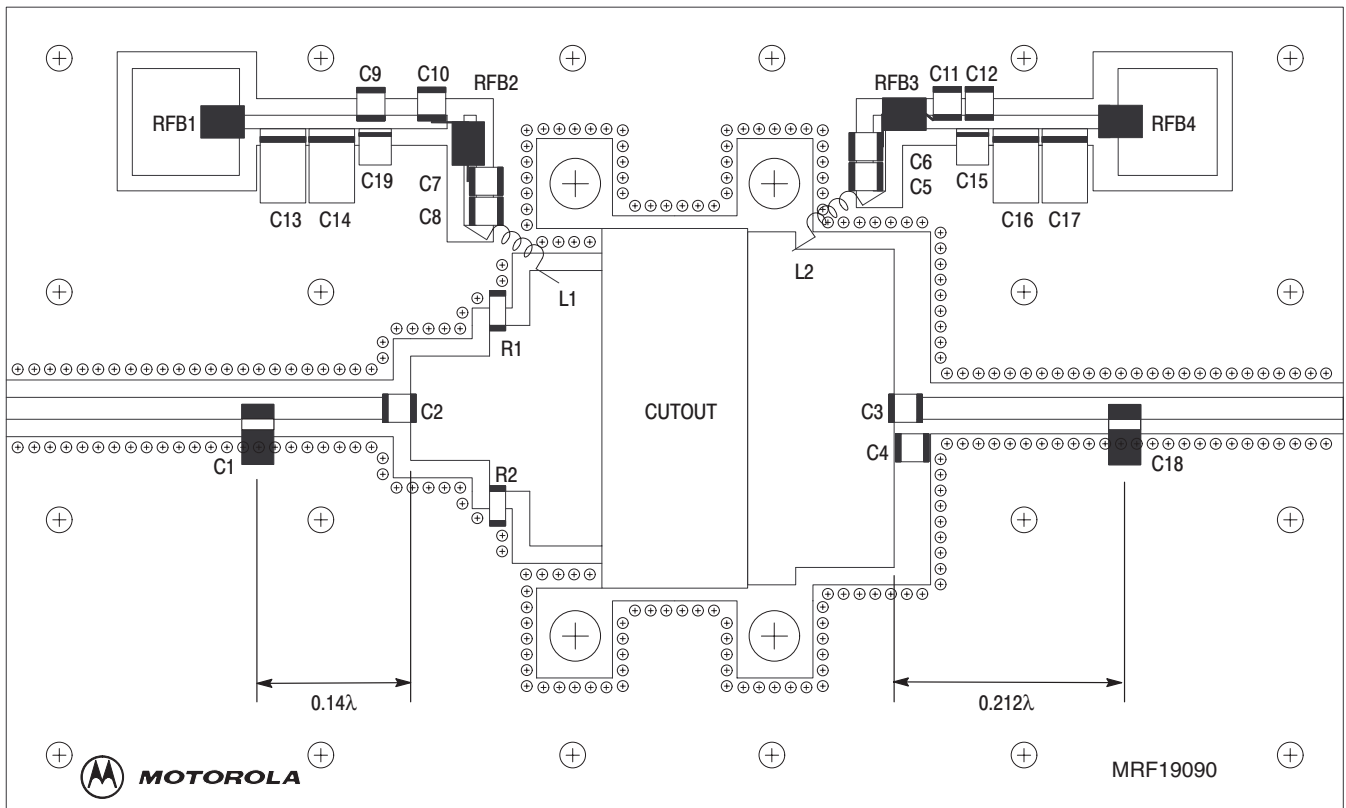


Figure 2. MRF19090 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

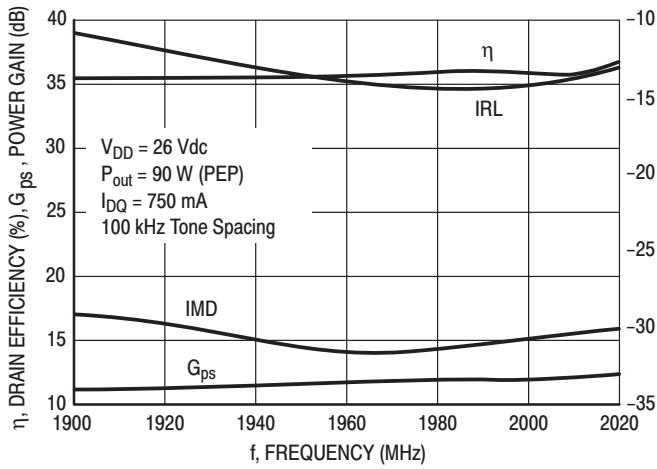


Figure 3. Class AB Performance versus Frequency

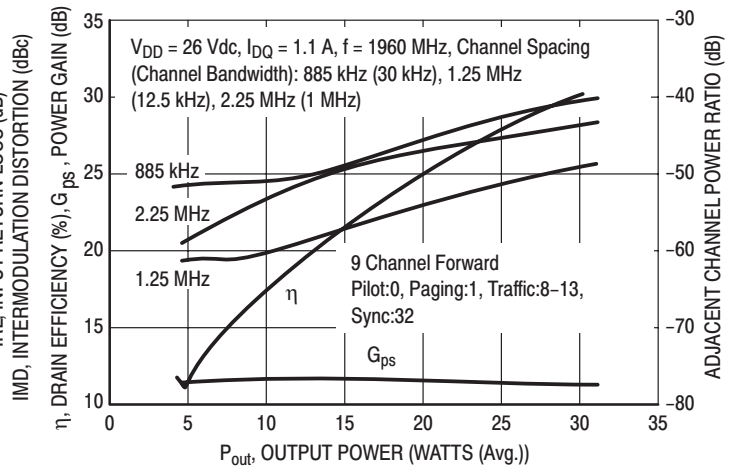


Figure 4. CDMA Performance ACPR, Gain and Drain Efficiency versus Output Power

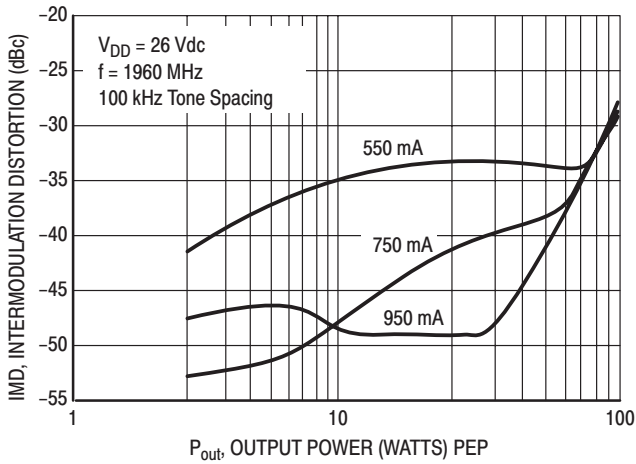


Figure 5. Third Order Intermodulation Distortion versus Output Power

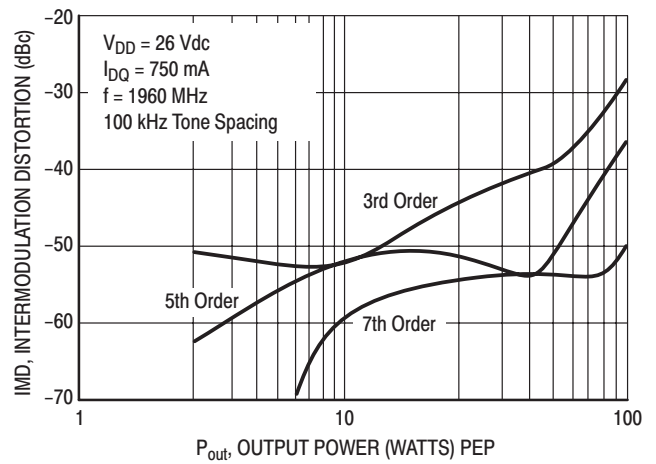


Figure 6. Intermodulation Products versus Output Power

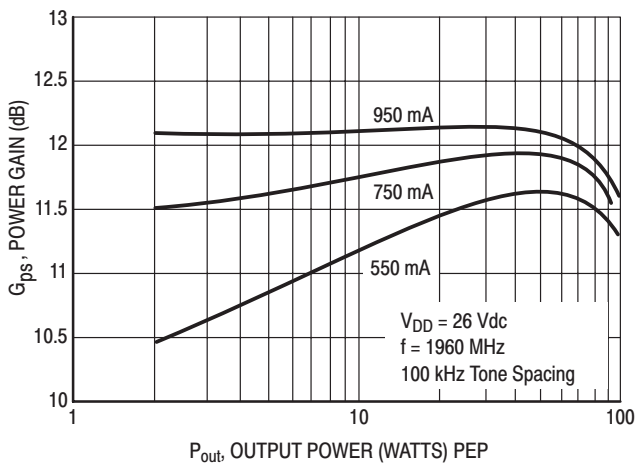


Figure 7. Power Gain versus Output Power

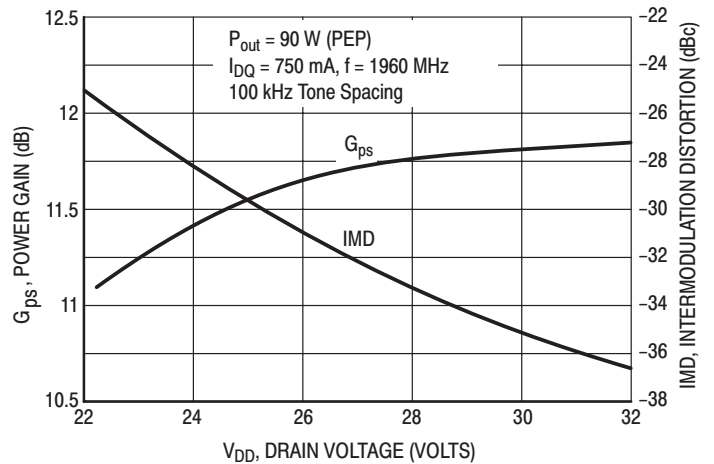
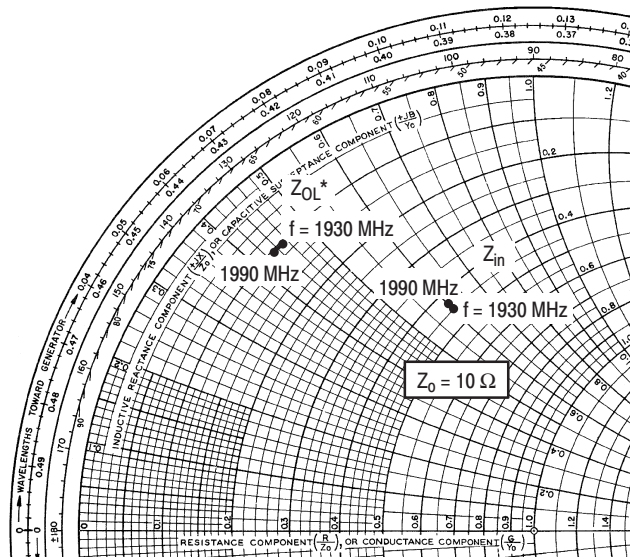


Figure 8. Third Order Intermodulation Distortion and Gain versus Supply Voltage



$V_{DD} = 26\text{ V}$, $I_{DQ} = 750\text{ mA}$, $P_{out} = 90\text{ Watts (PEP)}$

f MHz	Z_{in} Ω	Z_{OL}^* Ω
1930	$4.5 + j6.1$	$1.1 + j4.5$
1960	$4.4 + j6.0$	$1.1 + j4.4$
1990	$4.3 + j6.1$	$1.1 + j4.3$

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the optimum load impedance at a given output power, voltage, IMD, bias current and frequency.

Note: Z_{OL}^* was chosen based on tradeoffs between gain, output power, drain efficiency and intermodulation distortion.

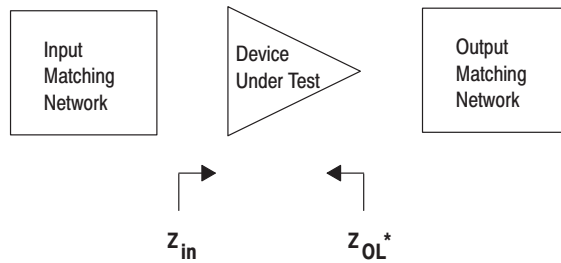
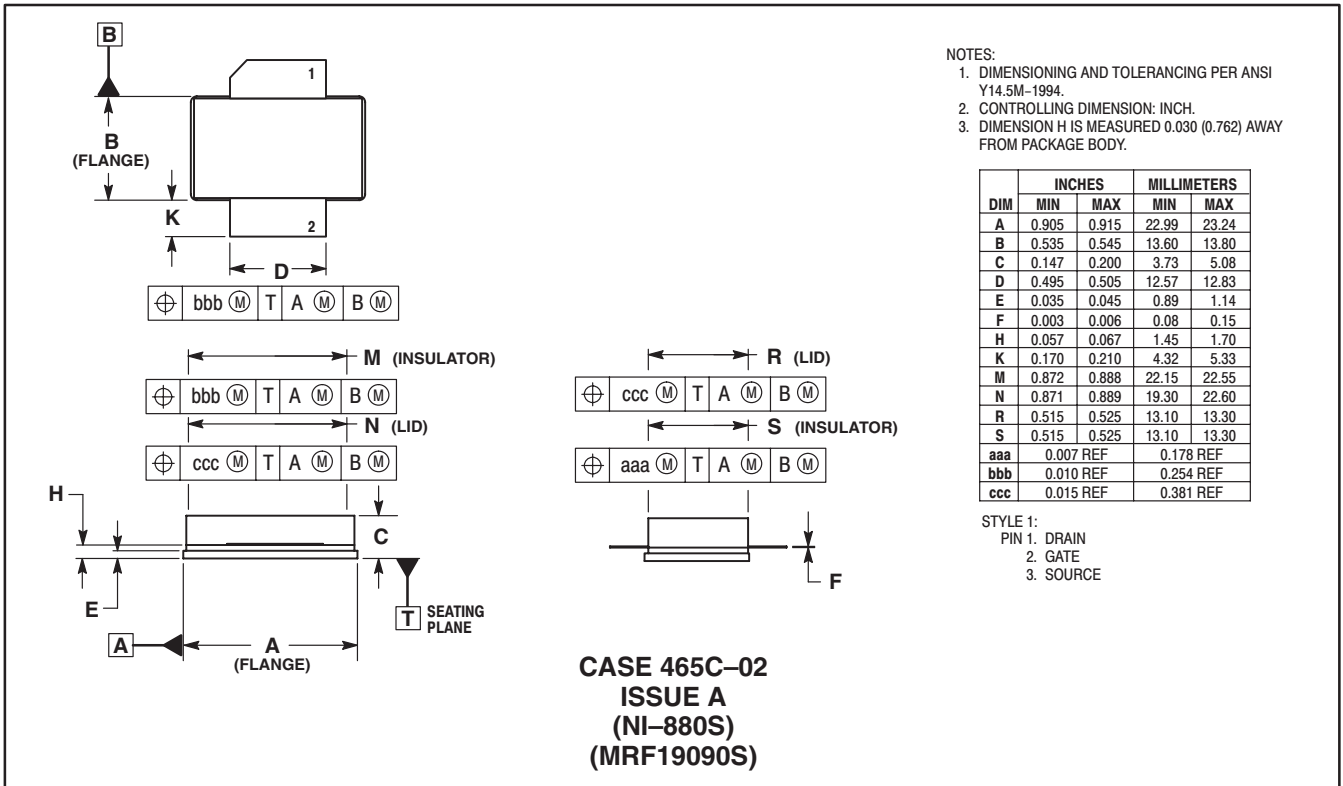
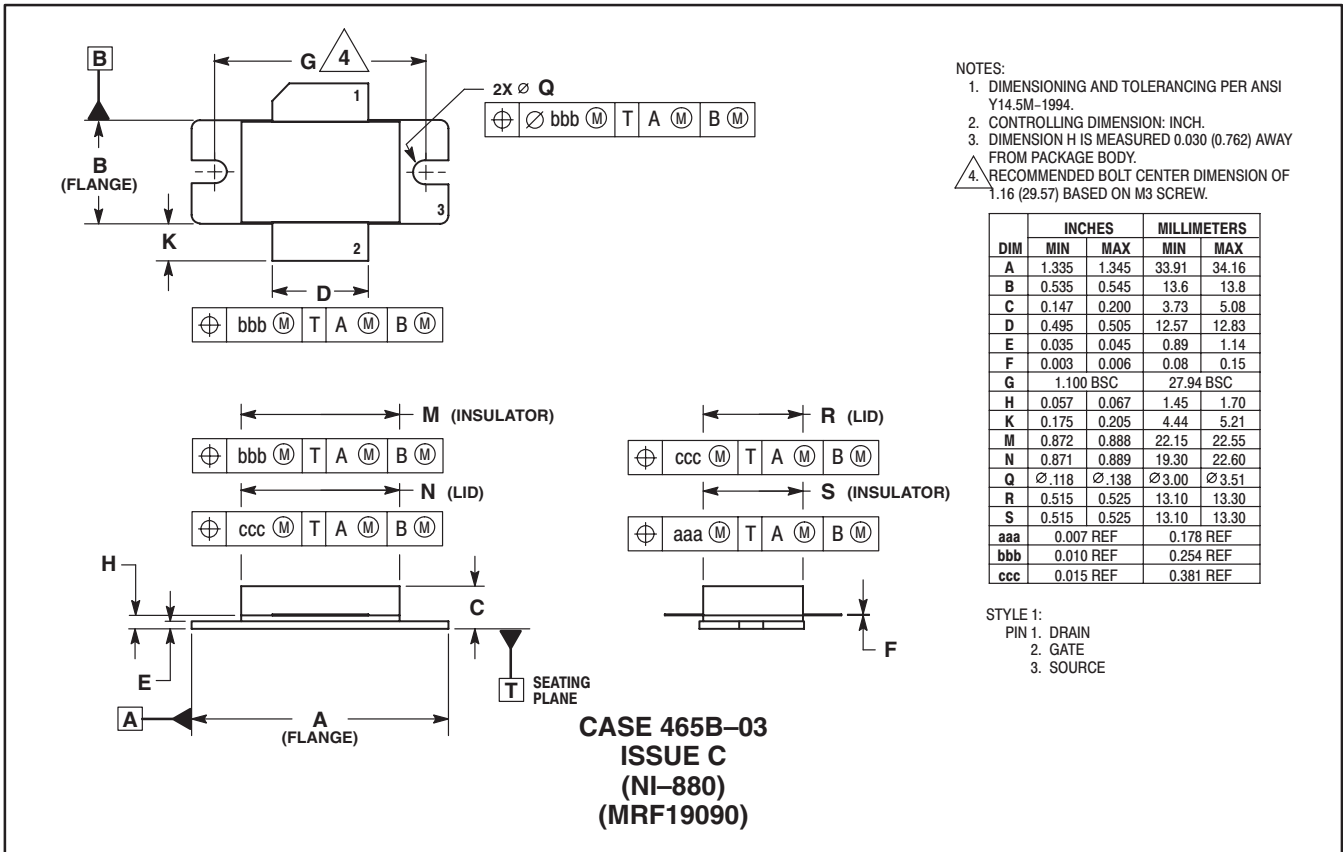



Figure 9. Series Equivalent Input and Output Impedance

PACKAGE DIMENSIONS



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